SEMiX® 5

3-Level NPC IGBT-Module

SEMiX155MLI07E4

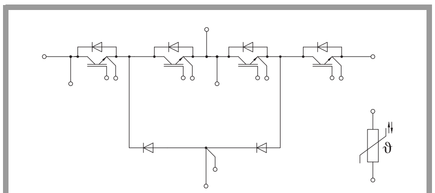
Target Data

Features

- Solderless assembling solution with PressFIT signal pins and screw power terminals
- IGBT 4 Trench Gate Technology
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Reliable mechanical design with injection moulded terminals and reliable internal connections
- UL recognized file no. E63532
- NTC temperature sensor inside

Remarks*

- Case temperature limited to T_C=125°C max
- Product reliability results are valid for T_{jop}=150°C
- IGBT1 : outer IGBTs T1 & T4
- IGBT2 : inner IGBTs T2 & T3
- Diode1 : outer diodes D1 & D4
- Diode2 : inner diodes D2 & D3
- Diode5 : clamping diodes D5 & D6
- For storage and case temperature with TIM see document “TP(HALA P8) SEMiX 5p”



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Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
IGBT1				
V_{CES}	T_j = 25 °C		650	V
I_C	T_j = 175 °C	T_c = 25 °C	187	A
		T_c = 80 °C	141	A
I_{Cnom}			150	A
I_{CRM}	I_{CRM} = 3 x I_{Cnom}		450	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 360 V, V_{GE} ≤ 15 V, T_j = 150 °C, V_{CES} ≤650 V		10	µs
T_j			-40 ... 175	°C
IGBT2				
V_{CES}	T_j = 25 °C		650	V
I_C	T_j = 175 °C	T_c = 25 °C	187	A
		T_c = 80 °C	141	A
I_{Cnom}			150	A
I_{CRM}	I_{CRM} = 3 x I_{Cnom}		450	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 360 V, V_{GE} ≤ 15 V, T_j = 150 °C, V_{CES} ≤ 650 V		10	µs
T_j			-40 ... 175	°C
Diode1				
V_{RRM}	T_j = 25 °C		650	V
I_F	T_j = 175 °C	T_c = 25 °C	145	A
		T_c = 80 °C	107	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2 x I_{Fnom}		200	A
I_{FSM}	10 ms, sin 180°, T_j = 25 °C		820	A
T_j			-40 ... 175	°C
Diode2				
V_{RRM}	T_j = 25 °C		650	V
I_F	T_j = 175 °C	T_c = 25 °C	145	A
		T_c = 80 °C	107	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2 x I_{Fnom}		200	A
I_{FSM}	10 ms, sin 180°, T_j = 25 °C		820	A
T_j			-40 ... 175	°C
Diode5				
V_{RRM}	T_j = 25 °C		650	V
I_F	T_j = 175 °C	T_c = 25 °C	145	A
		T_c = 80 °C	107	A
I_{Fnom}			100	A
I_{FRM}	I_{FRM} = 2 x I_{Fnom}		200	A
I_{FSM}	10 ms, sin 180°, T_j = 25 °C		820	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			300	A
T_{stg}	module without TIM		-40 ... 125	°C
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

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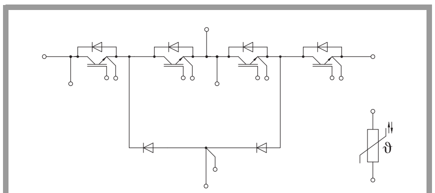

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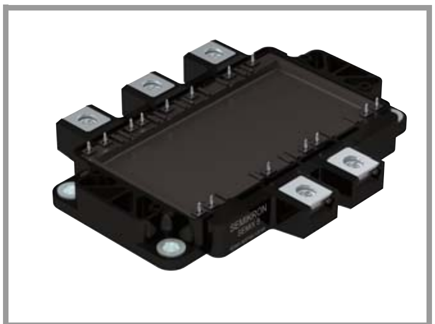
Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT1						
$V_{CE(sat)}$	I_C = 150 A, V_{GE} = 15 V, chiplevel	T_j = 25 °C		1.55	1.95	V
		T_j = 150 °C		1.75	2.15	V
V_{CE0}	chiplevel	T_j = 25 °C		0.90	1.00	V
		T_j = 150 °C		0.82	0.90	V
r_{CE}	V_{GE} = 15 V, chiplevel	T_j = 25 °C		4.3	6.3	mΩ
		T_j = 150 °C		6.2	8.3	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 4 mA		5.1	5.8	6.4	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 650 V, T_j = 25 °C				-	mA
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V	f = 1 MHz		9.2		nF
C_{oes}		f = 1 MHz		0.58		nF
C_{res}		f = 1 MHz		0.27		nF
Q_G	V_{GE} = -15 V...+15 V			1200		nC
R_{Gint}	T_j = 25 °C			2.0		Ω
$t_{d(on)}$	I_C = 100 A, V_{GE} = +15/-15 V					ns
t_r						ns
E_{on}				1		mJ
$t_{d(off)}$						ns
t_f						ns
E_{off}				6		mJ
$R_{th(j-c)}$	per IGBT				0.32	K/W
$R_{th(c-s)}$	per IGBT (λgrease=0.81 W/(m*K))			0.07		K/W
$R_{th(c-s)}$	per IGBT, pre-applied phase change material			TBD		K/W
IGBT2						
$V_{CE(sat)}$	I_C = 150 A, V_{GE} = 15 V, chiplevel	T_j = 25 °C		1.55	1.95	V
		T_j = 150 °C		1.75	2.15	V
V_{CE0}	chiplevel	T_j = 25 °C		0.90	1.00	V
		T_j = 150 °C		0.82	0.90	V
r_{CE}	V_{GE} = 15 V, chiplevel	T_j = 25 °C		4.3	6.3	mΩ
		T_j = 150 °C		6.2	8.3	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 4 mA		5.1	5.8	6.4	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 650 V, T_j = 25 °C				-	mA
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V	f = 1 MHz		9.2		nF
C_{oes}		f = 1 MHz		0.58		nF
C_{res}		f = 1 MHz		0.27		nF
Q_G	V_{GE} = -15 V...+15 V			1200		nC
R_{Gint}	T_j = 25 °C			2.0		Ω
$t_{d(on)}$	I_C = 100 A, V_{GE} = +15/-15 V					ns
t_r						ns
E_{on}				1		mJ
$t_{d(off)}$						ns
t_f						ns
E_{off}				6		mJ
$R_{th(j-c)}$	per IGBT				0.32	K/W
$R_{th(c-s)}$	per IGBT (λgrease=0.81 W/(m*K))			0.07		K/W
$R_{th(c-s)}$	per IGBT, pre-applied phase change material			TBD		K/W



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Remarks*

- Case temperature limited to T_C=125°C max
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- IGBT1 : outer IGBTs T1 & T4
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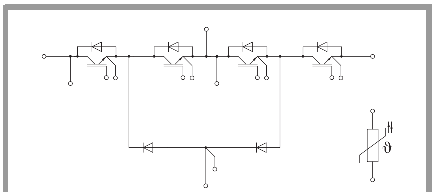

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Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Diode1						
$V_F = V_{EC}$	I_F = 100 A V_{GE} = 0 V chiplevel	T_j = 25 °C		1.40	1.76	V
		T_j = 150 °C		1.38	1.77	V
V_{F0}	chiplevel	T_j = 25 °C		1.04	1.24	V
		T_j = 150 °C		0.85	0.99	V
r_F	chiplevel	T_j = 25 °C		3.6	5.3	mΩ
		T_j = 150 °C		5.3	7.8	mΩ
I_{RRM}	I_F = 100 A			-		A
Q_{rr}				-		µC
E_{rr}	V_{GE} = +15/-15 V			2.25		mJ
$R_{th(j-c)}$	per diode				0.51	K/W
$R_{th(c-s)}$	per diode (λgrease=0.81 W/(m*K))			0.12		K/W
$R_{th(c-s)}$	per diode, pre-applied phase change material			TBD		K/W
Diode2						
$V_F = V_{EC}$	I_F = 100 A V_{GE} = 0 V chiplevel	T_j = 25 °C		1.40	1.76	V
		T_j = 150 °C		1.38	1.77	V
V_{F0}	chiplevel	T_j = 25 °C		1.04	1.24	V
		T_j = 150 °C		0.85	0.99	V
r_F	chiplevel	T_j = 25 °C		3.6	5.3	mΩ
		T_j = 150 °C		5.3	7.8	mΩ
I_{RRM}	I_F = 100 A					A
Q_{rr}						µC
E_{rr}	V_{GE} = +15/-15 V			-		mJ
$R_{th(j-c)}$	per diode				0.51	K/W
$R_{th(c-s)}$	per diode (λgrease=0.81 W/(m*K))			0.12		K/W
$R_{th(c-s)}$	per diode, pre-applied phase change material			TBD		K/W
Diode5						
$V_F = V_{EC}$	I_F = 100 A chiplevel	T_j = 25 °C		1.40	1.76	V
		T_j = 150 °C		1.38	1.77	V
V_{F0}	chiplevel	T_j = 25 °C		1.04	1.24	V
		T_j = 150 °C		0.85	0.99	V
r_F	chiplevel	T_j = 25 °C		3.6	5.3	mΩ
		T_j = 150 °C		5.3	7.8	mΩ
I_{RRM}	I_F = 100 A					A
Q_{rr}						µC
E_{rr}	V_{GE} = +15/-15 V			3		mJ
$R_{th(j-c)}$	per diode				0.51	K/W
$R_{th(c-s)}$	per diode (λgrease=0.81 W/(m*K))			0.12		K/W
$R_{th(c-s)}$	per diode, pre-applied phase change material			TBD		K/W

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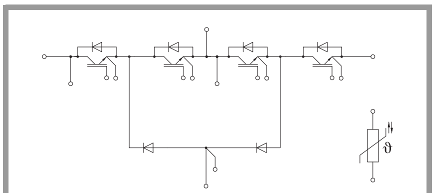

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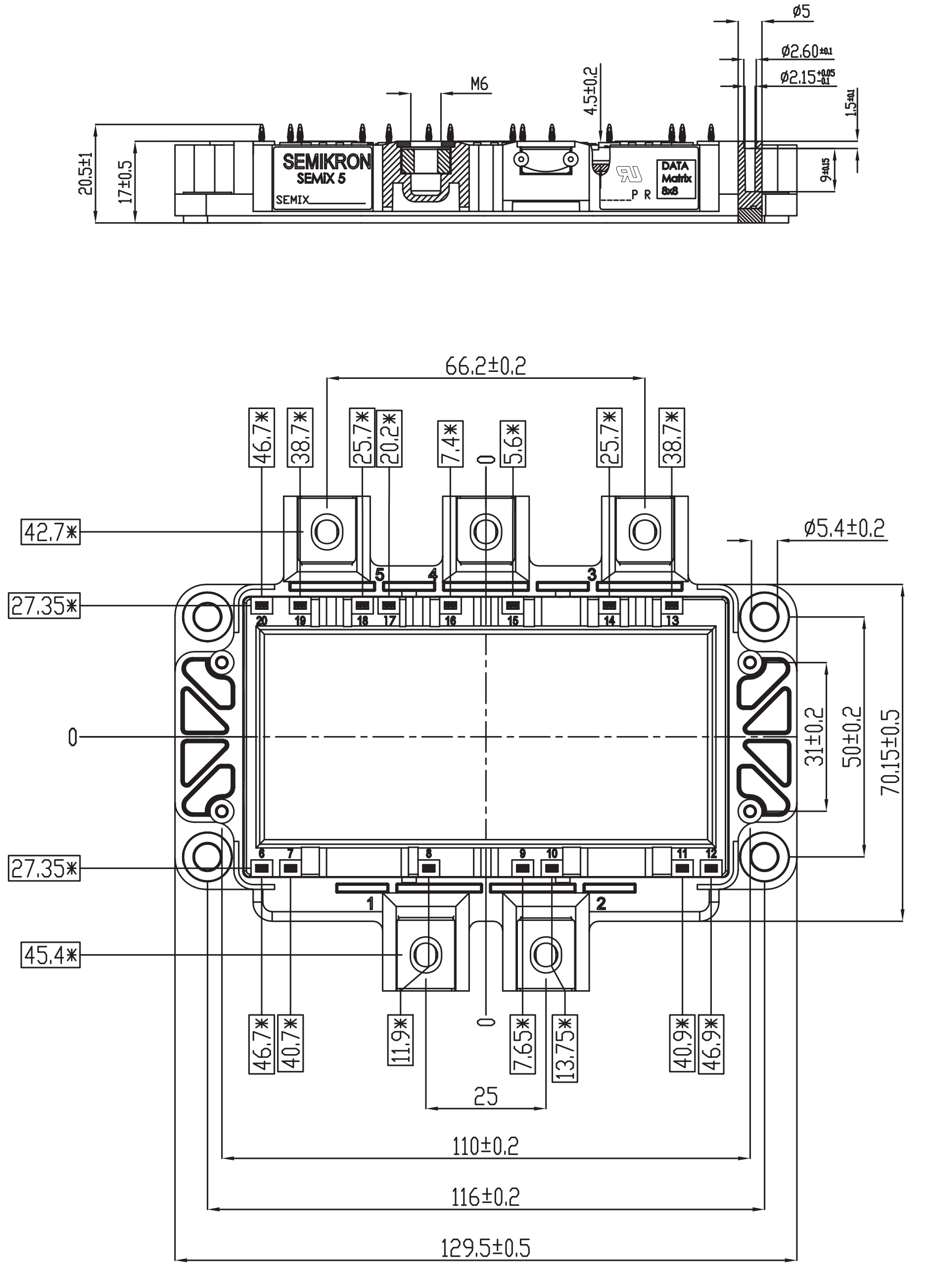
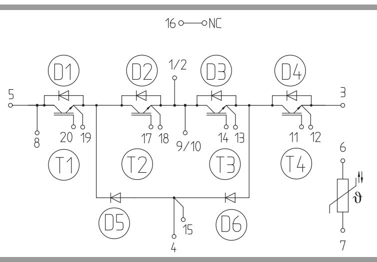
Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
Module						
L_{sCE1}				32		nH
L_{sCE2}				t.b.d.		nH
$R_{CC'+EE'}$	measured between terminal 5 and 1	T_C = 25 °C		1.2		mΩ
		T_C = 125 °C		1.65		mΩ
$R_{th(c-s)1}$	calculated without thermal coupling			0.009		K/W
$R_{th(c-s)2}$	including thermal coupling, Ts underneath module (λ_{grease}=0.81 W/(m*K))			t.b.d.		K/W
$R_{th(c-s)2}$	including thermal coupling, Ts underneath module, pre-applied phase change material			t.b.d.		K/W
M_s	to heat sink (M5)		3		6	Nm
M_t		to terminals (M6)	3		6	Nm
						Nm
w				398		g
Temperature Sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			3550 ±2%		K



* = All dimension with tolerance of ⌖ Ø 0.4

For technical details please refer
to SEMiX(R)5 Mounting Instruction

SEMiX5p



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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